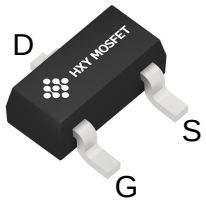
HXY2320MI

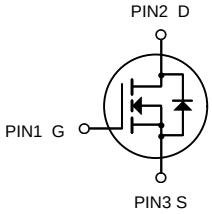
N-Channel Enhancement Mode MOSFET

Description

The HXY2320MI uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V.
This device is suitable for use as a Battery protection or in other Switching application.



SOT-23-3L



N-Channel MOSFET

General Features

V_{DS} = 20V,I_D = 8A
$R_{DS(ON)}$ < 13mΩ @ V_{GS}=4.5V
$R_{DS(ON)}$ < 22.5mΩ@ V_{GS}=2.5V

Application

High power and current handing capability
Lead free product is acquired
Surface mount package
PWM applications

Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HXY2320MI	SOT23-3L	2320	3000PCS

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	±12	V
I_D	Drain Current-Continuous	8	A
I_{DM}	Drain Current-Pulsed	32	A
P_D	Maximum Power Dissipation	2	W
T_J,T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	°C
$R_{\theta JA}$	Thermal Resistance,Junction-to-Ambient	120	°C/W

Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=20V, V_{GS}=0V,	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS}=0V, V_{GS} =±12V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	0.5	0.75	1.2	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note2	V_{GS}=4.5V, I_D=8A	-	11	13	mΩ
		V_{GS}=2.5V, I_D=5A	-	16	22.5	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=10V, V_{GS}=0V, f=1.0MHz	-	700	-	pF
C_{oss}	Output Capacitance		-	132	-	pF
C_{rss}	Reverse Transfer Capacitance		-	114	-	pF
Q_g	Total Gate Charge	V_{DS}=10V, I_D=4A, V_{GS}=4.5V	-	15	-	nC
Q_{gs}	Gate-Source Charge		-	2	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	5.2	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=10V, I_D=4A, R_{GEN}=3Ω, V_{GS}=4.5V	-	9	-	ns
t_r	Turn-on Rise Time		-	25	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	37	-	ns
t_f	Turn-off Fall Time		-	14	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	8	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	32	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S=8A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Performance Characteristics

Figure 1: Output Characteristics

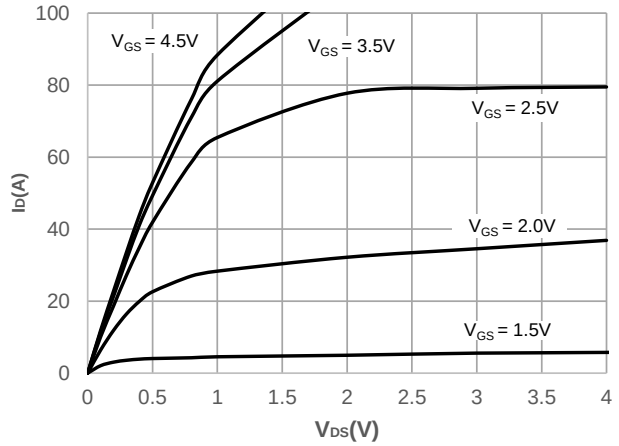


Figure 2: Typical Transfer Characteristics

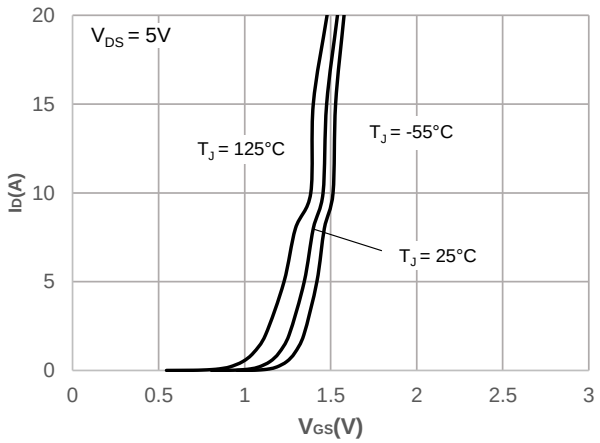


Figure 3: On-resistance vs. Drain Current

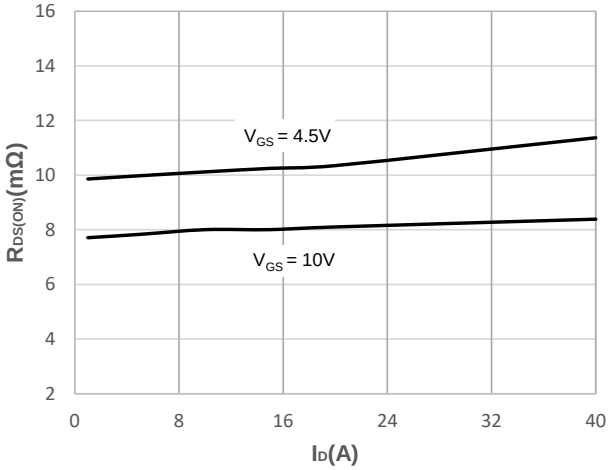


Figure 4: Body Diode Characteristics

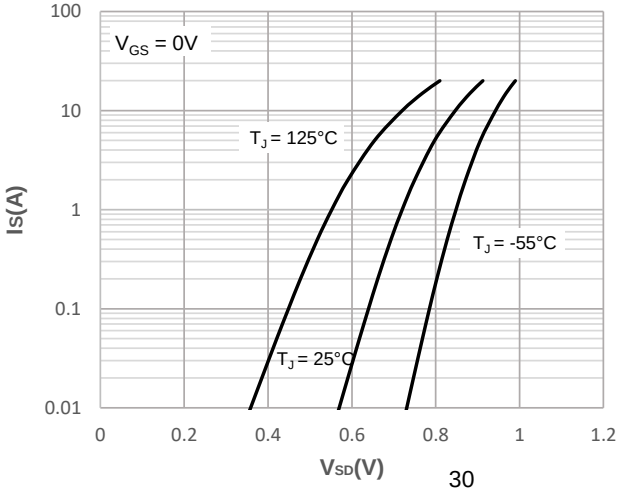


Figure 5: Gate Charge Characteristics

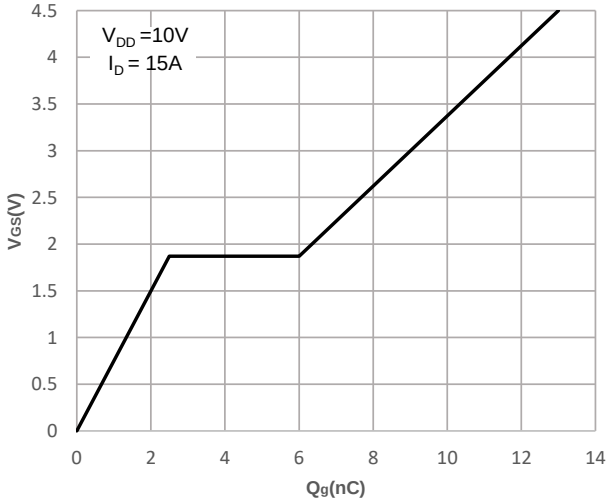


Figure 6: Capacitance Characteristics

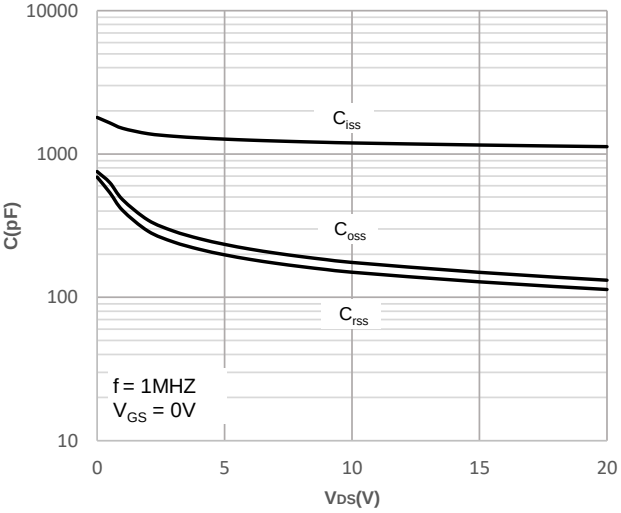


Figure 7: Normalized Breakdown voltage vs. Junction Temperature

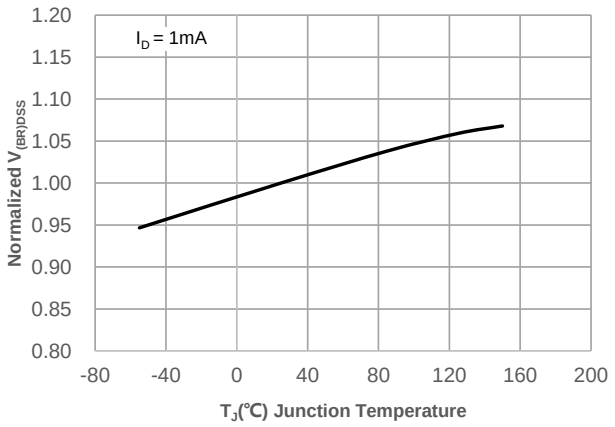


Figure 8: Normalized on Resistance vs. Junction Temperature

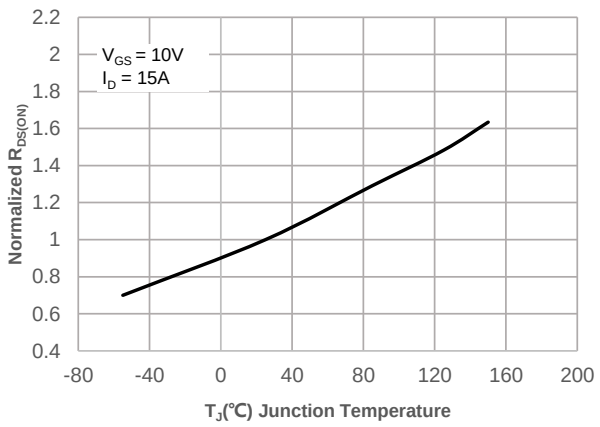


Figure 9: Maximum Safe Operating Area

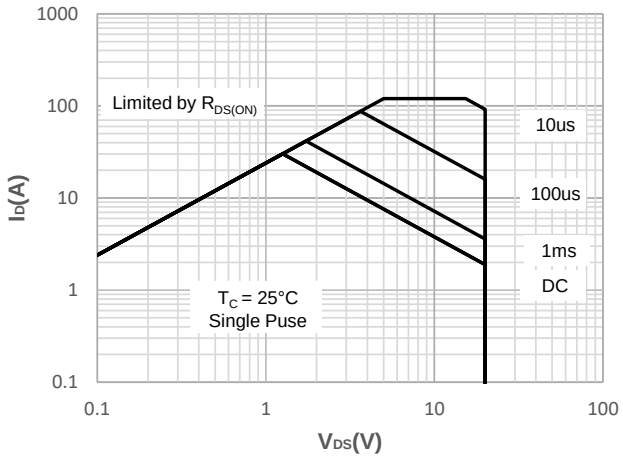


Figure 10: Maximum Continuous Drian Current vs. Case Temperature

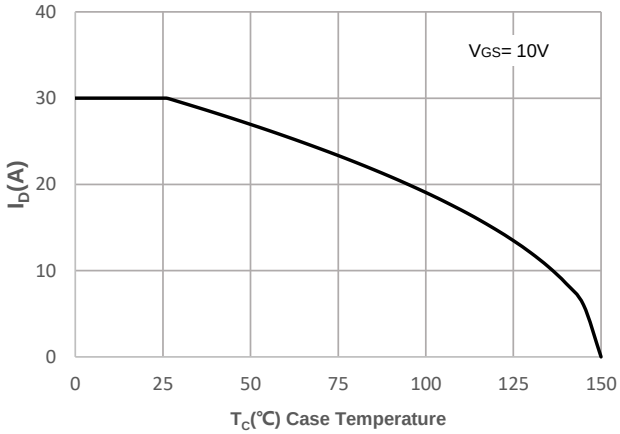


Figure 11: Normalized Maximum Transient Thermal Impedance

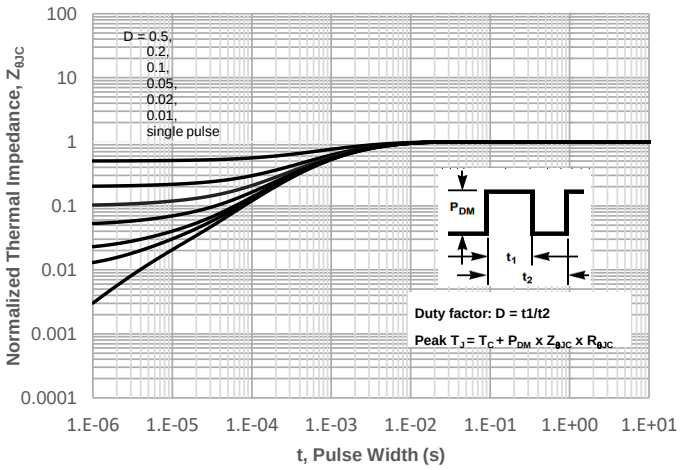
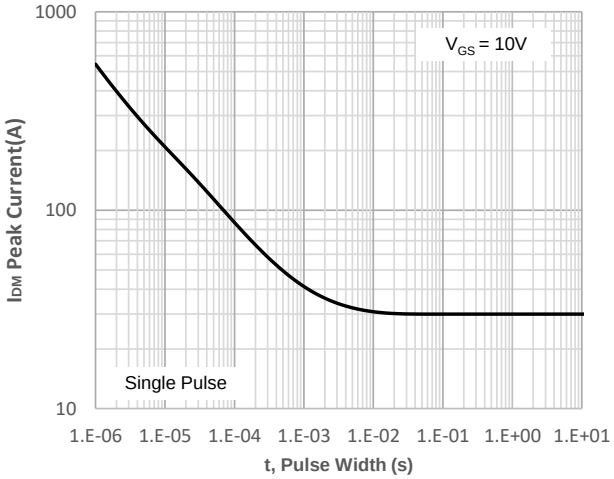
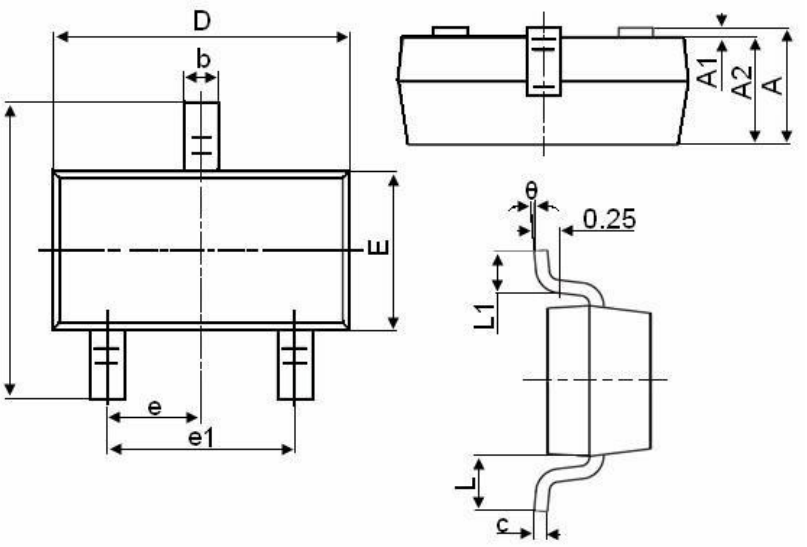


Figure 12: Peak Current Capacity



SOT-23-3L Package Information



Symbol	Dimensions in Millimeters	
	Min.	Max.
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.300	0.500
c	0.100	0.200
D	2.800	3.000
E	1.500	1.700
E1	2.650	2.950
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.600
θ	0°	8°

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